IN THE CLAIMS

Please amend the claims as follows:

The following claim set replaces all prior versions, and listings, of claims in the application:

1. 24. *(Currently Amended)* A method of fabricating an electroluminescent device including the steps of:

a)   implanting a surface region of a silicon wafer, doped with a donor impurity to render the wafer n-type, with an acceptor impurity such that the surface region has a volume concentration of the acceptor impurity which is greater than a volume concentration of the donor impurity;

b)   anodizing the wafer under illumination to produce a luminescent porous silicon region extending through the surface region; and

c)   depositing an electrode on the porous silicon region;

wherein ~~the~~a condition (i) is satisfied, wherein condition (i) requires that at least a part of the region has an acceptor impurity volume concentration comparable with the solid solubility limit of the acceptor impurity in silicon ~~is satisfied~~;

~~and/or~~and wherein ~~one or more~~at least one of the following conditions are satisfied:

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(ii)   the surface region has a sheet resistivity greater than 100 Ω ~~m⁻~~per

square immediately prior to the anodizing step;

(iii)   less than 1% of the acceptor impurity is electrically active prior to

the anodizing step;

(iv)   the silicon wafer does not receive an anneal between steps (a) and

(b); and

(v)   the anodization step (b) causes surface doping of silicon quantum

wires within the porous silicon region, rendering the surface doped quantum wires

p-type.

25. *(Currently Amended)* A method of fabricating an electroluminescent device

according to claim 24, wherein, ~~when one or more~~at least one of conditions (ii) to (v)

apply, and the anodization step (b) comprises the step of anodizing the wafer in aqueous

hydrofluoric acid in such a manner that microporous porous silicon is formed.

26-31. *(Withdrawn from consideration)*